

Ref #	Hits	Search Query	DBs	Default Operat or	Plural s	Time Stamp
L1	31558	(ion near5 conduct\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/15 15:39
L2	10083	1 and electrolyte	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/15 15:39
L3	9098	2 and electrode	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/15 14:42
L4	6693	3 and oxide	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/15 14:42
L5	1182	4 and (inuslat\$3 dielectric)	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/15 14:43
L6	1097	5 and (via hole trench open\$3 contact groove recess)	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/15 14:45
L7	833	6 and (silver copper Ag Au)	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/15 14:45
L8	569	7 and (tungsten W)	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/15 14:47
L9	347	8 and (semiconductor memory)	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/15 14:48
L10	15485	(ion near5 conduct\$3)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 15:39
L11	0	10 and electrolyte	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/15 15:40
L12	0	10 and chalcogenide	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/15 15:40